

**TO-263**

- $R_{DS(ON)}$ ( at  $V_{GS}=6V$ ) <5.5mohm
- 100% EAS Tested <6.5mohm
- 100%  $\nabla VDS$  Tested

### General Description

- Split gate trench MOSFET technology
- Excellent package for heat dissipation
- High density cell design for low  $R_{DS(ON)}$
- Moisture Sensitivity Level 1
- Epoxy Meets UL 94 V-0 Flammability Rating
- Halogen Free

### Applications

- Power switching application
- Uninterruptible power supply
- DC-DC convertor

### ■ Absolute Maximum Ratings ( $T_A=25^\circ C$ unless otherwise noted)

Parameter		Symbol	Limit	Unit
Drain-source Voltage		$V_{DS}$	100	V
Gate-source Voltage		$V_{GS}$	$\pm 20$	V
Drain Current	$T_A=25$	$I_D$	15	A
	$T_A=100$		9	
	$T_C=25$		130	
	$T_C=100$		82	
Pulsed Drain Current <sup>A</sup>		$I_{DM}$	520	A
Avalanche energy <sup>B</sup>		EAS	290	mJ
Total Power Dissipation <sup>C</sup>	$T_A=25$	$P_D$	2.7	W
	$T_A=100$		1.1	
	$T_C=25$		178	
	$T_C=100$		71	
Junction and Storage Temperature Range		$T_J, T_{STG}$	-55~+150	

### ■ Thermal resistance

Parameter		Symbol	Typ	Max	Units
Thermal Resistance Junction-to-Ambient <sup>D</sup>	Steady-State	$R_{\theta JA}$	35	45	/W
Thermal Resistance Junction-to-Case	Steady-State	$R_{\theta JC}$	0.55	0.7	

### ■ Ordering Information (Example)

PREFERRED P/N	PACKING CODE	Marking	MINIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE
YJB130G10B	F2	YJB130G10B	800	/	8000	13" reel



# YJB130G10B

## ■ Electrical Characteristics (T<sub>J</sub>=25°C unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
<b>Static Parameter</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =250μA	100	-	-	V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =100V, V <sub>GS</sub> =0V	-	-	1	μA
		V <sub>DS</sub> =100V, V <sub>GS</sub> =0V, T <sub>J</sub> =150	-	-	100	
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V	-	-	±100	nA
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250μA	2	2.8	4	V
Static Drain-Source On-Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =65A	-	4	5.5	mΩ
		V <sub>GS</sub> =10V, I <sub>D</sub> =20A	-	4	5.5	
		V <sub>GS</sub> =6V, I <sub>D</sub> =20A	-	5	6.5	
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> =65A, V <sub>GS</sub> =0V	-	0.9	1.2	V
Gate resistance	R <sub>G</sub>	f=1MHz, Open drain	-	0.8	-	Ω
Maximum Body-Diode Continuous Current	I <sub>S</sub>		-	-	130	A
<b>Dynamic Parameters</b>						
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =50V, V <sub>GS</sub> =0V, f=1MHz	-	4300	-	pF
Output Capacitance	C <sub>oss</sub>		-	2000	-	
Reverse Transfer Capacitance	C <sub>riss</sub>		-	25	-	
<b>Switching Parameters</b>						
Total Gate Charge	Q <sub>g</sub>	V <sub>GS</sub> =10V, V <sub>DS</sub> =50V, I <sub>D</sub> =65A	-	60	-	nC
Gate-Source Charge	Q <sub>gs</sub>		-	17	-	
Gate-Drain Charge	Q <sub>gd</sub>		-	19	-	
Reverse Recovery Charge	Q <sub>rr</sub>	I <sub>F</sub> =65A, di/dt=600A/us	-	170	-	nC
Reverse Recovery Time	t <sub>rr</sub>		-	40	-	ns
Turn-on Delay Time	t <sub>D(on)</sub>	V <sub>GS</sub> =10V, V <sub>DD</sub> =50V, I <sub>D</sub> =65A R <sub>GEN</sub> =2.2Ω	-	20	-	ns
Turn-on Rise Time	t <sub>r</sub>		-	100	-	
Turn-off Delay Time	t <sub>D(off)</sub>		-	30	-	
Turn-off fall Time	t <sub>f</sub>		-	8	-	

A. Repetitive rating; pulse width limited by max. junction temperature.

B. T<sub>J</sub>=25 , V<sub>DD</sub>=50V, V<sub>G</sub>=10V, R<sub>G</sub>=25Ω, L=0.5mH, I<sub>AS</sub>=34A.

C. P<sub>d</sub> is based on max. junction temperature, using junction-case thermal resistance.

D. The value of R<sub>θJA</sub> is measured with the device mounted on 1in2 FR-4 board with 2oz. Copper, in a still air environment with T<sub>A</sub>=25 . The maximum allowed junction temperature of 150 . The value in any given application depends on the user's specific board design.



# YJB130G10B

## Typical Electrical and Thermal Characteristics Diagrams

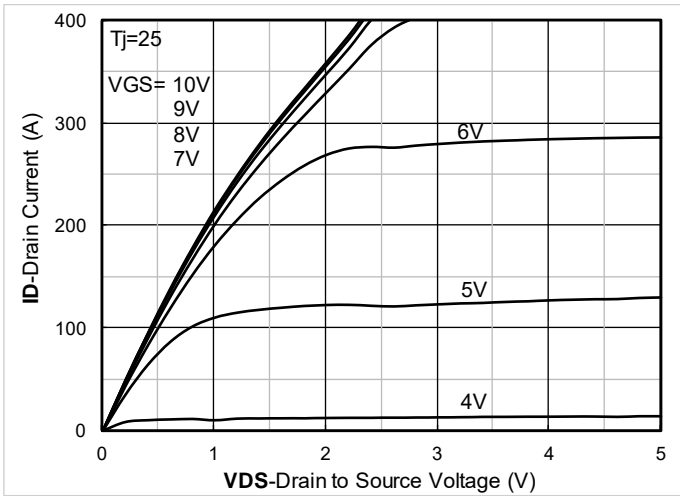


Figure1. Output Characteristics

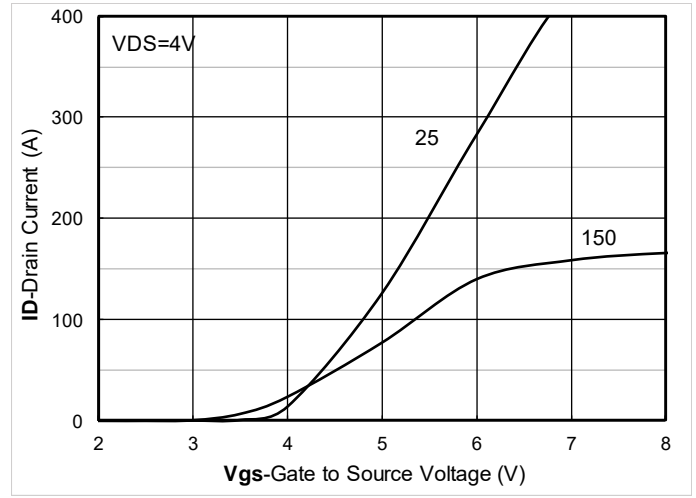


Figure2. Transfer Characteristics

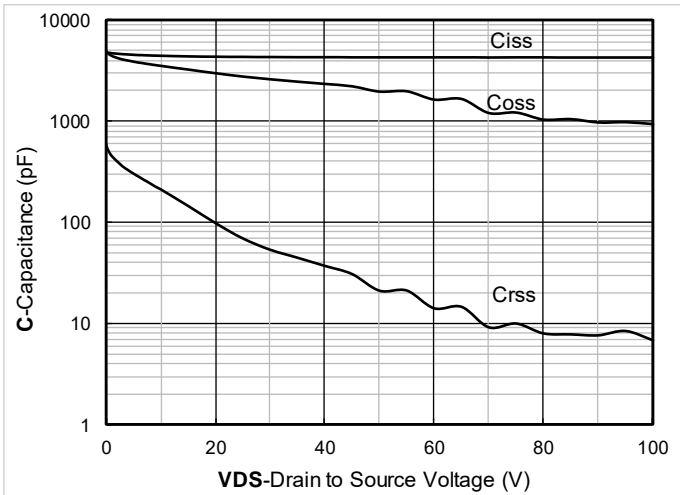


Figure3. Capacitance Characteristics

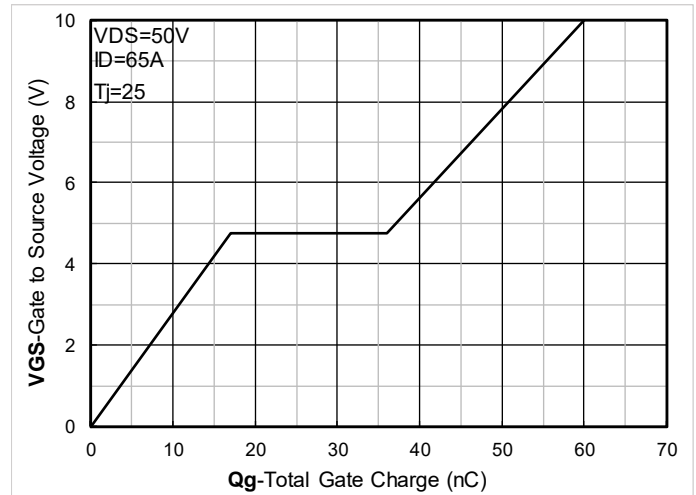


Figure4. Gate Charge

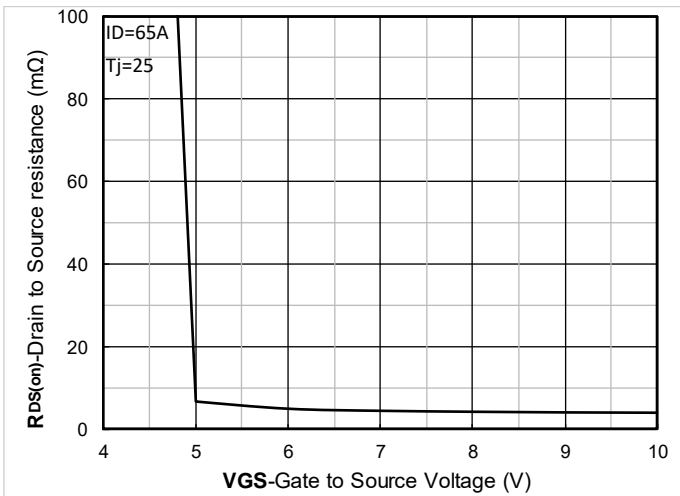


Figure5. On-Resistance vs Gate to Source Voltage

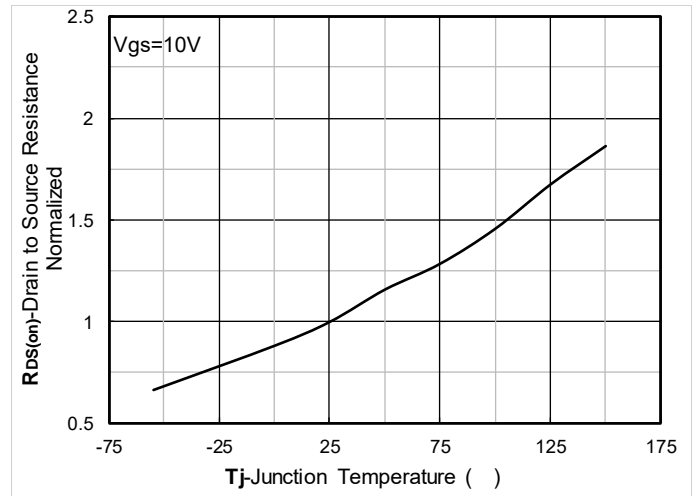


Figure6. Normalized On-Resistance



# YJB130G10B

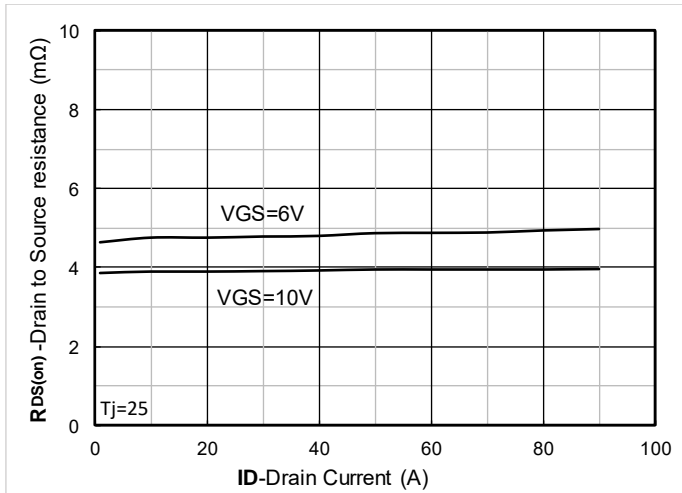


Figure7. RDS(on) VS Drain Current

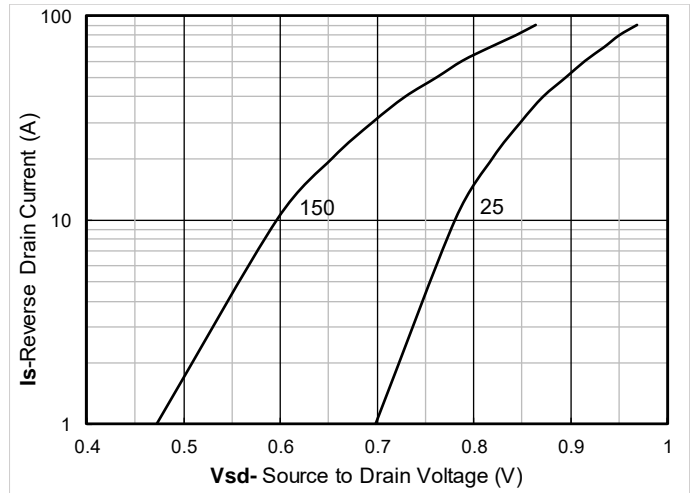


Figure8. Forward characteristics of reverse diode

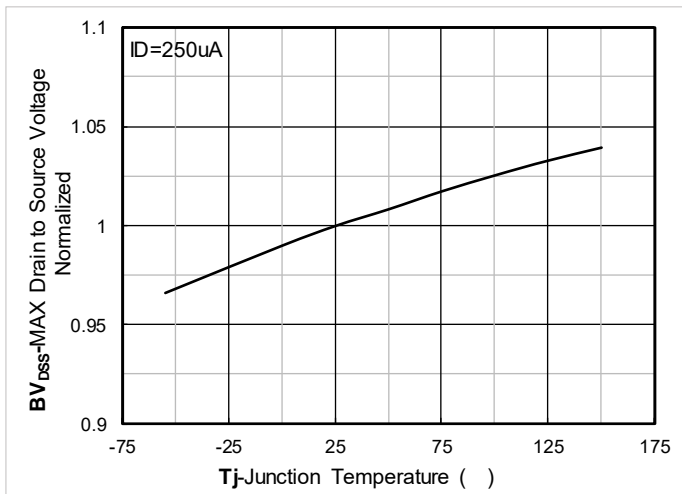


Figure9. Normalized breakdown voltage

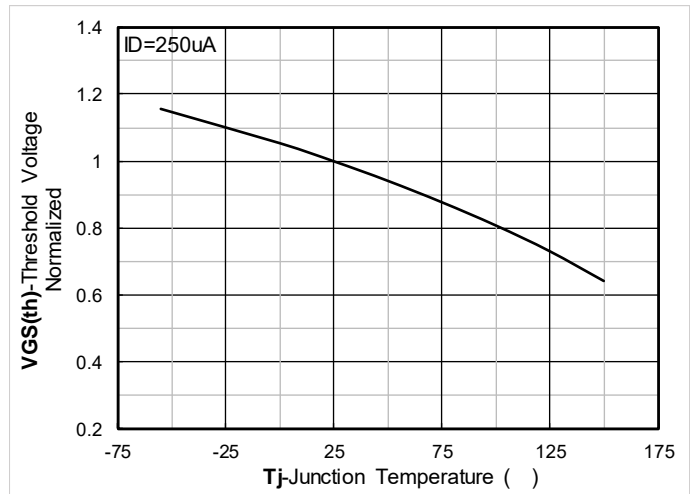


Figure10. Normalized Threshold voltage

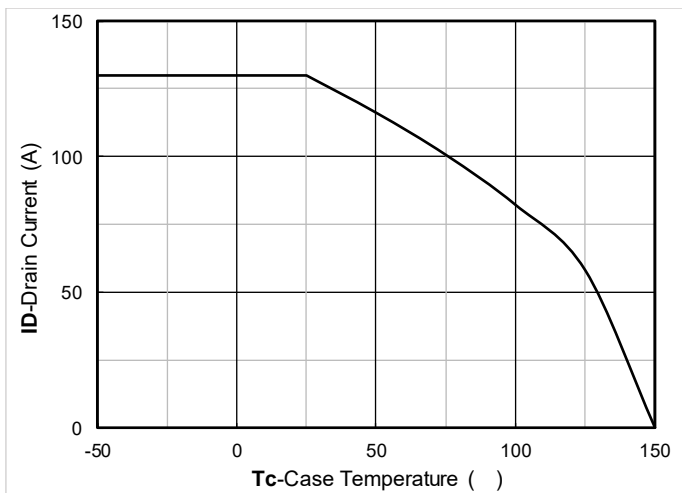


Figure11. Current dissipation

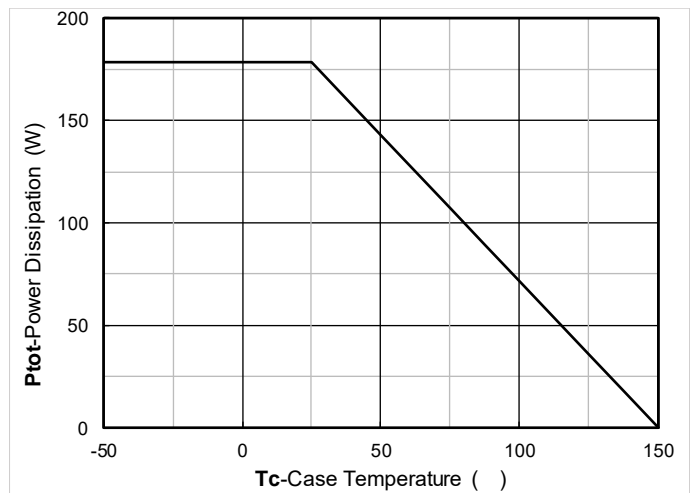


Figure12. Power dissipation

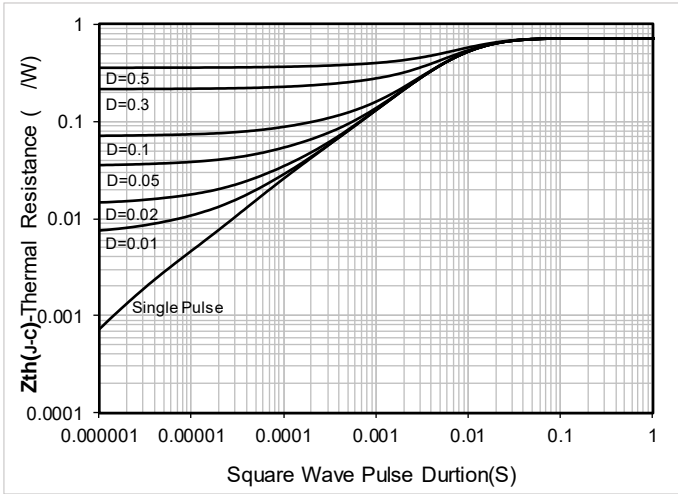


Figure13. Maximum Transient Thermal Impedance

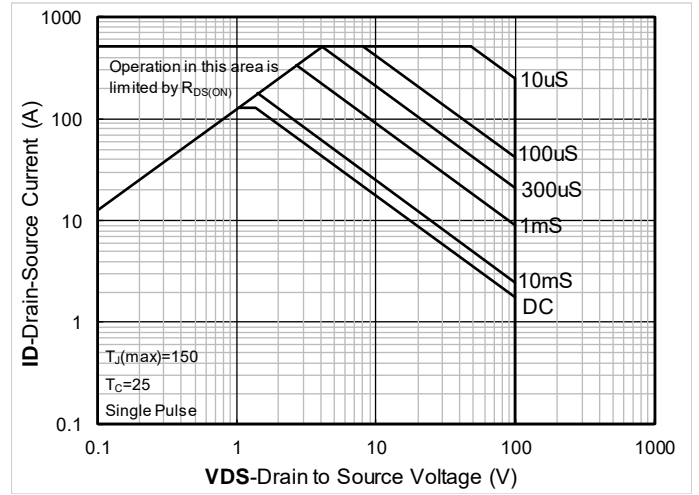


Figure14. Safe Operation Area

## ■ Test Circuits & Waveforms

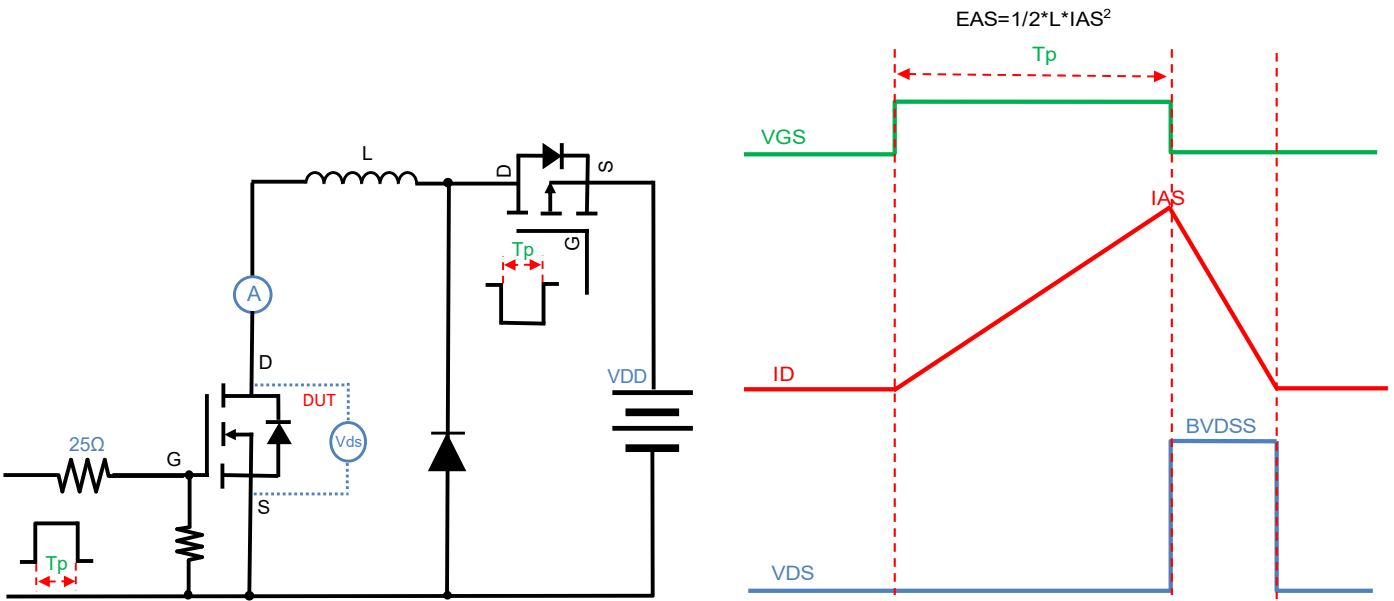


Figure A. Unclamped Inductive Switching (UIS) Test Circuit & Waveform

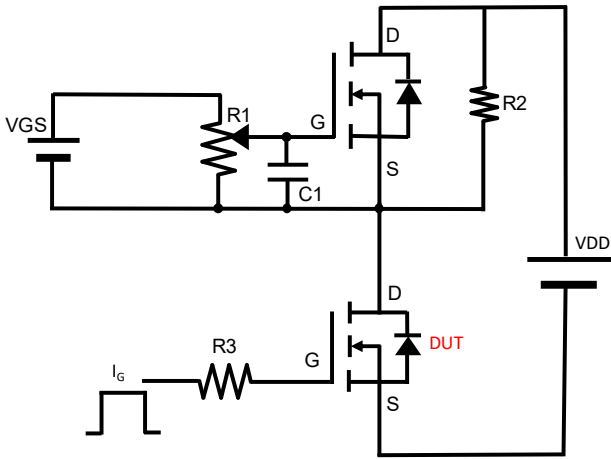


Figure B. Gate Charge Test Circuit & Waveform

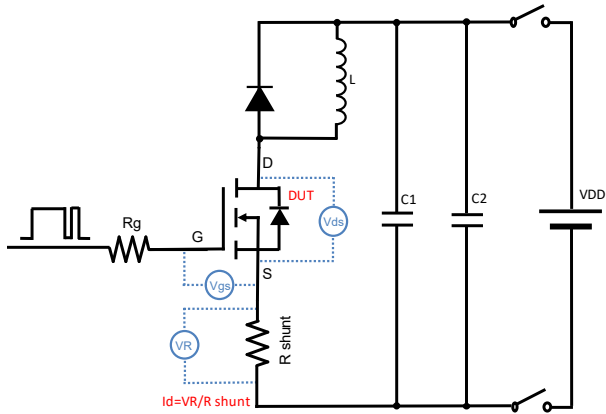


Figure C. Resistive Switching Test Circuit & Waveform

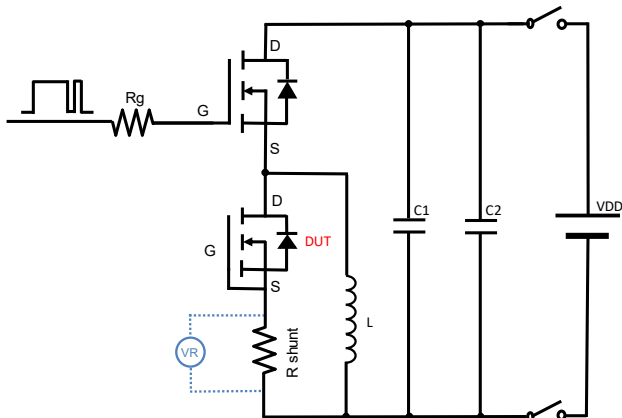


Figure D. Diode Recovery Test Circuit & Waveform





## YJB130G10B

---

### Disclaimer

The information presented in this document is for reference only. Yangzhou Yangjie Electronic Technology Co., Ltd. reserves the right to make changes without notice for the specification of the products displayed herein to improve reliability, function or design or otherwise.

The product listed herein is designed to be used with ordinary electronic equipment or devices, and not designed to be used with equipment or devices which require high level of reliability and the malfunction of which would directly endanger human life (such as medical instruments, transportation equipment, aerospace machinery, nuclear-reactor controllers, fuel controllers and other safety devices), Yangjie or anyone on its behalf, assumes no responsibility or liability for any damages resulting from such improper use of sale.

This publication supersedes & replaces all information previously supplied. For additional information, please visit our website <http://www.21yangjie.com> , or consult your nearest Yangjie's sales office for further assistance.